

Pb Free Plating Product

MUR4020PR thru MUR40120PR



40.0 Ampere Heatsink Dual Doubler Polarity Ultra Fast Recovery Rectifiers

Features ※ ThinkSemi latest&matured process FRD ※ Low forward voltage drop ※ High current capability ※ Low reverse leakage current ※ High surge current capability Application ※ Automotive Inverters and Solar Inverters ※ Car Audio Amplifiers and Sound Device Systems ※ Plating Power Supply, Motor Control, UPS and SMPS etc. Mechanical Data ※ Case: Heatsink open metal TO-3P(TO-3PN/TO-3PB) package ※ Epoxy: UL 94V-0 rate flame retardant ※ Terminals: Solderable per MIL-STD-202 method 208 ※ Polarity: As marked on diode body ※ Mounting position: Any ※ Weight: 6.5 gram approximately	TO-3P(TO-3PN-SQ) Unit: inch(mm) ① ② ③ Case Positive Common Cathode Suffix "PT" ① ② ③ Case Negative Common Anode Suffix "PA" ① ② ③ Case Doubler Polarity Suffix "PR" ① ② ③ Case Series Connection Suffix "PL"
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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

PARAMETER	SYMBOL	MUR4020PR	MUR4030PR MUR4040PR	MUR4060PR	MUR4080PR	MUR40100PR	MUR40120PR	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	200	400	600	800	1000	1200	V
Maximum RMS Voltage	VRMS	140	280	420	560	700	840	V
Maximum DC Blocking Voltage	VDC	200	400	600	800	1000	1200	V
Maximum Average Forward Rectified Current TC=125℃ (Total Device 2x20.0A=40.0A)	IF(AV)	40.0						A
Peak Forward Surge Current, 8.3ms single Half sine-wave superimposed on rated load (JEDEC method)(Per Diode/Per Leg)	IFSM	400						A
Maximum Instantaneous Forward Voltage @20.0A(Per Diode/Per Leg)	VF (Typical)	0.90-1.10	1.10-1.40	1.40-1.80	1.40-1.80			V
Maximum DC Reverse Current @TJ=25℃ At Rated DC Blocking Voltage @TJ=125℃	IR	5.0 500						μA μA
Maximum Reverse Recovery Time (Note1)	Trr	35-50			50-75			nS
Typical Junction Capacitance (Note 2)	CJ	200						pF
Typical Thermal Resistance (Note 3)	RθJC	0.75						℃/W
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 to +175						℃

Note:(1)Reverse recovery test conditions IF = 0.5A, IR = 1.0A, Irr = 0.25A.

Note:(2)Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts DC.

Note:(3)Thermal Resistance junction to case.

FIG.1 - FORWARD CURRENT DERATING CURVE

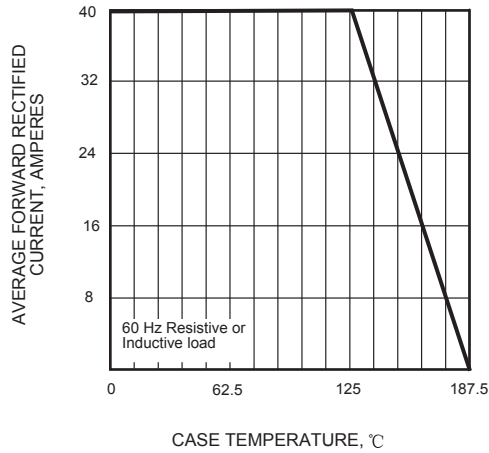


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

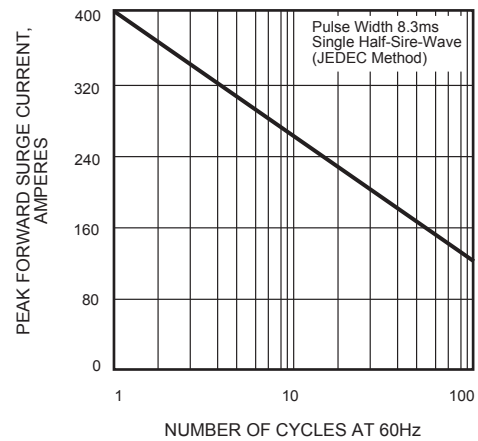


FIG.3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

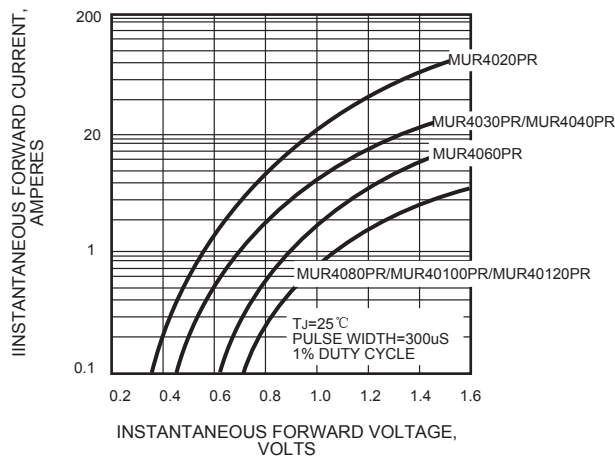


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

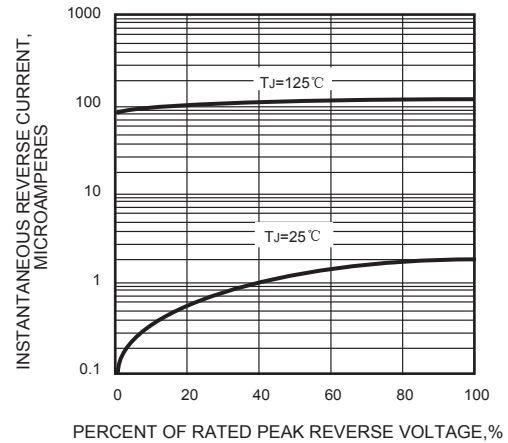


FIG.5 - TYPICAL JUNCTION CAPACITANCE

